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Kind regards,

Team Nexperia

# PEMD30; PUMD30

NPN/PNP double resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

Rev. 01 — 31 March 2006

**Product data sheet** 

### 1. Product profile

### 1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP/PNP	NPN/NPN	
	Philips	JEITA	complement	complement	
PEMD30	SOT666	-	PEMB30	PEMH30	
PUMD30	SOT363	SC-88	PUMB30	PUMH30	

#### 1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs

- Cost-saving alternative for BC847BPN and BC847BVN
- Switching loads

### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor; for the PNP transistor	with negative pol	arity			
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



# 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
FIII	Description	Simplified outline	Зуппон
1	GND (emitter) TR1		
2	input (base) TR1	6   5   4	6 5 4
3	output (collector) TR2		R1
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R1
			1 2 3
			006aaa269

# 3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PEMD30	-	plastic surface-mounted package; 6 leads	SOT666		
PUMD30	SC-88	plastic surface-mounted package; 6 leads	SOT363		

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD30	2U
PUMD30	*B3

<sup>[1] \* = -:</sup> made in Hong Kong

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		• •			
Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative pol	arity		
$V_{\text{CBO}}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	-	5	V
I <sub>O</sub>	output current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> _	200	mW
	SOT666		[1][2]	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		[1][2]	300	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

### 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> _	-	625	K/W
	SOT666		[1][2]	-	625	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1][2]	-	416	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

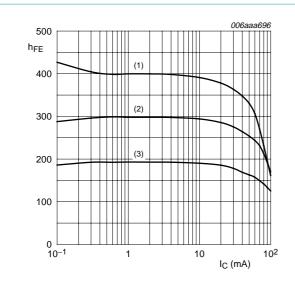
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

u						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor; for the PNP transi	stor with negative polarity				
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 20 \text{ mA}$	30	-	-	
$V_{\text{CEsat}}$	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF



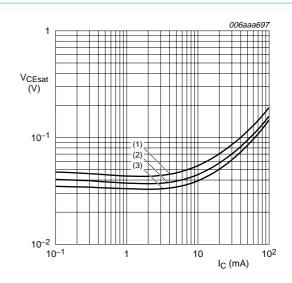
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \,^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



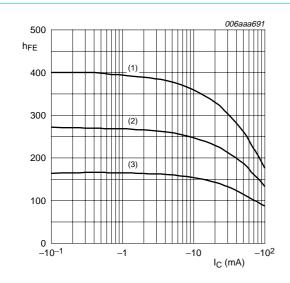
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

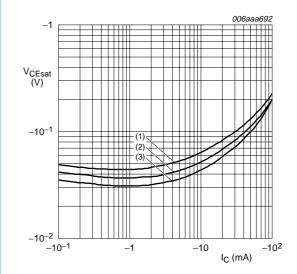


$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 3. TR2 (PNP): DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

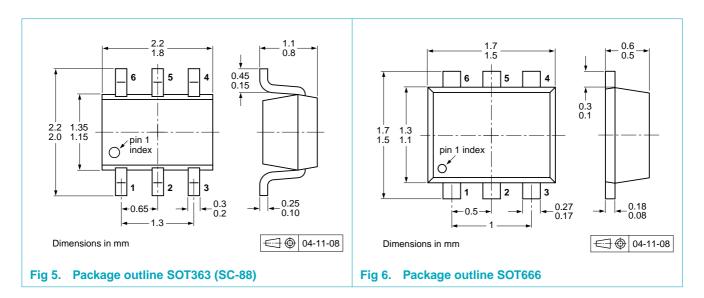
(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

# 8. Package outline



# 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

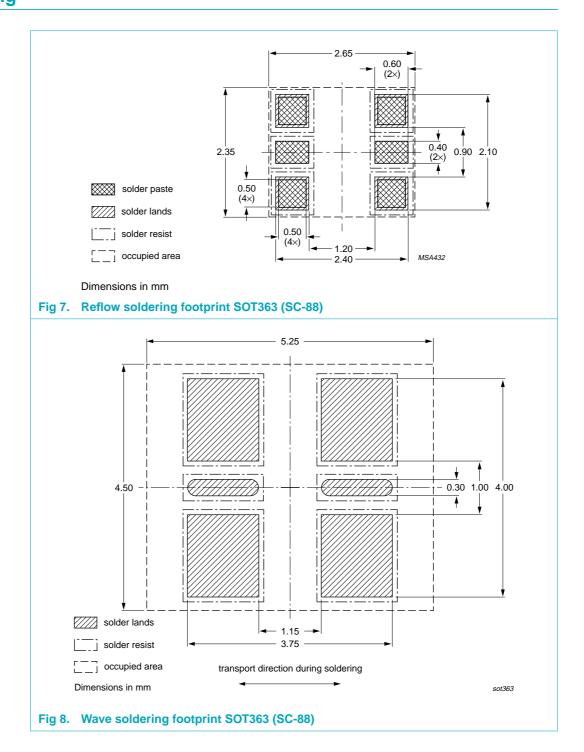
Type number Packag		Description		Packing quantity			
			3000	4000	8000	10000	
PEMD30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-	
		4 mm pitch, 8 mm tape and reel	-	-115	-	-	
PUMD30	SOT363	4 mm pitch, 8 mm tape and reel; T1	<u>2</u> -115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	<u>3</u> ] -125	-	-	-165	

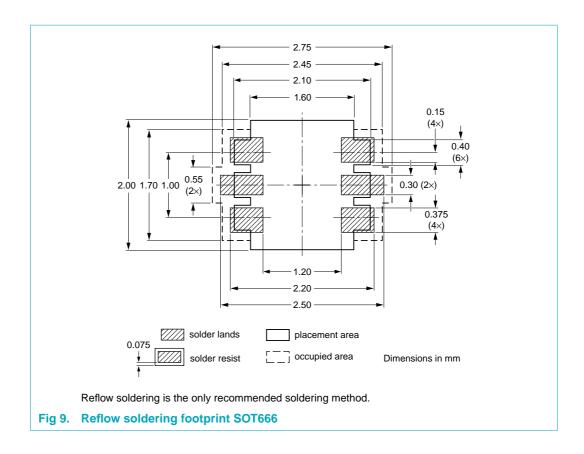
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

[2] T1: normal taping

[3] T2: reverse taping

# 10. Soldering





PEMD30; PUMD30

NPN/PNP double resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = open

# 11. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD30_PUMD30_1	20060331	Product data sheet	-	-

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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